



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	12mΩ @ V _{GS} = 10V	10A
30V	16mΩ @ V _{GS} = 4.5V	8.5A

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

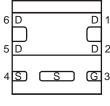
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)

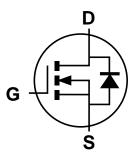
U-DFN2020-6 (Type E)



Bottom View



Pin Out



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LFDE-7	U-DFN2020-6 (Type E)	3,000/Tape & Reel
DMN3016LFDE-13	U-DFN2020-6 (Type E)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



NR = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Z		Ι		J	K	L	М	N	0	Р	R
•												
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



NR = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Kev

Date Code Key												
Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	2		0	1	2	3	4	5	6	7	8	9
Week	1-26			27-52				53				
Code		Α	-Z			a	-Z			7	<u> </u>	
Internal Code	Sun	ı	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	٧	Х		Υ		Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V	Steady State	T _A = +25°C T _A = +70°C	ID	10 8	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s		ID	12 9	А
Maximum Continuous Body Diode Forward Curre	nt (Note 6)		Is	2.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1		I _{DM}	90	Α	
Avalanche Current (Note 7) L = 0.1mH		I _{AS}	22	А	
Avalanche Energy (Note 7) L = 0.1mH			Eas	24	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Bower Discipation (Note 5)	T _A = +25°C	D-	0.73	W
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.47	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	171	°C/W
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	RθJA	121	C/VV
Total Power Dissipation (Note 6)	$T_A = +25$ °C	Pp	2.02	W
Total Fower Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	1.30	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	62	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	9.3	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

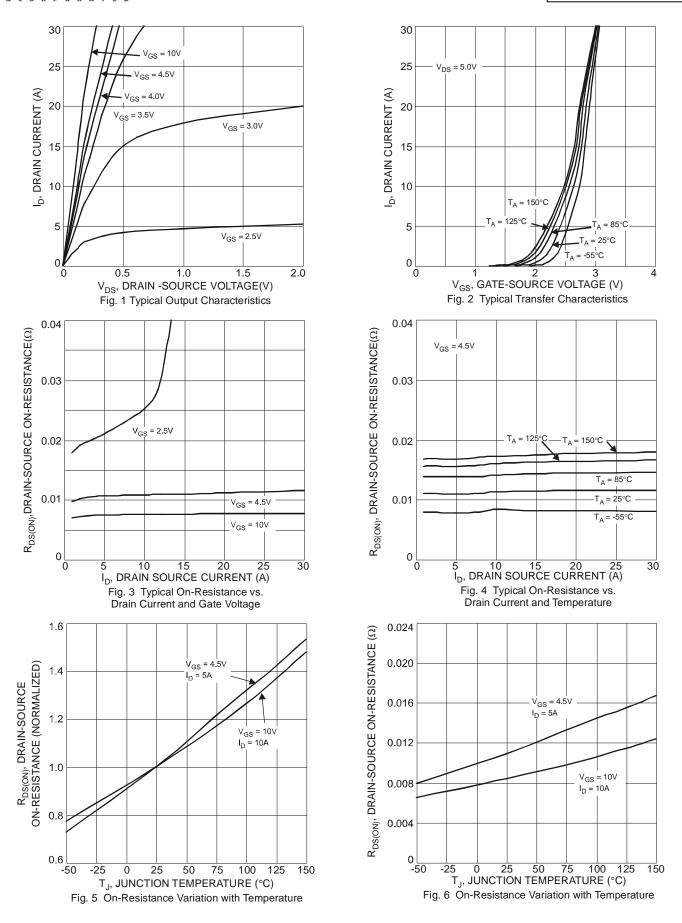
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.4	_	2.0	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	Dagger	-	8	12	mΩ	VGS = 10V, ID = 11A
Static Dialit-Source Off-Resistance	R _{DS(ON)}	1	12	16	11122	$V_{GS} = 4.5V, I_{D} = 9A$
Forward Transfer Admittance	Y _{fs}	_	32		S	V _{DS} = 5V, I _D = 12A
Diode Forward Voltage	V _{SD}	_	0.70	1.0	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	1415			15)/ 1/ 0)/
Output Capacitance	Coss	_	119	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	82	_		I = I.OWHZ
Gate Resistance	Rg	_	2.6	3.2	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (VGS = 4.5V)	Qg	_	11.3	_		
Total Gate Charge (VGS = 10V)	Qg	_	25.1	_	nC	V 45V L 40A
Gate-Source Charge	Qgs	_	3.5	_	nc	$V_{DS} = 15V, I_{D} = 12A$
Gate-Drain Charge	Qgd	_	3.6	_		
Turn-On Delay Time	td(on)	_	4.8	_		
Turn-On Rise Time	t _R	_	16.5	_	20	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}	_	26.1	_	ns	$R_L = 1.25\Omega$, $R_G = 3\Omega$
Turn-Off Fall Time	tr		5.6	_		
Reverse Recovery Time	trr		12.3	_	ns	104 11/14 5004/
Reverse Recovery Charge	Q _{RR}	_	10.4	_	nC	IF = 12A, di/dt = 500A/μs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Is and Ess ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







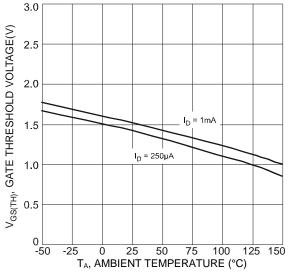
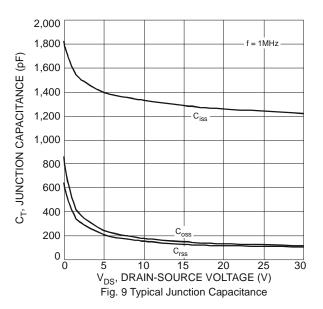
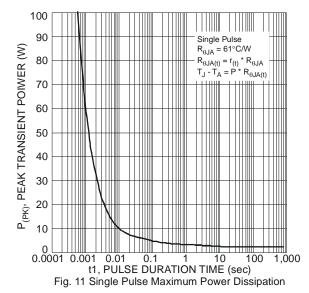
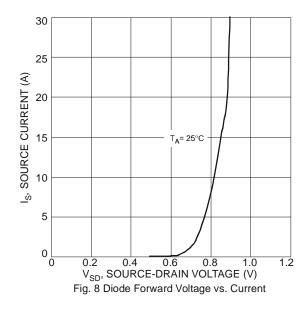
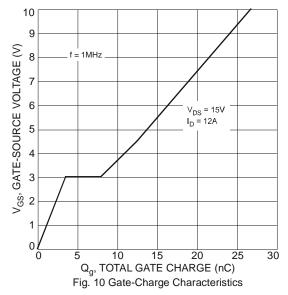


Fig. 7 Gate Threshold Variation vs. Ambient Temperature











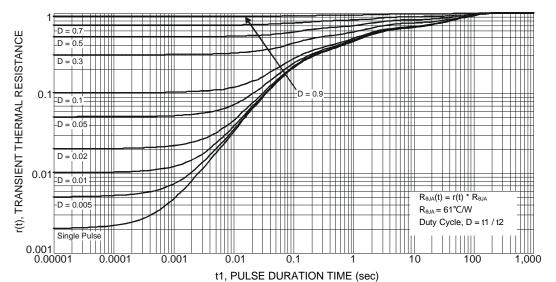


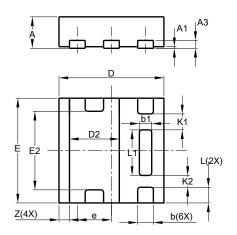
Fig. 12 Transient Thermal Resistance



Package Outline Dimension

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)

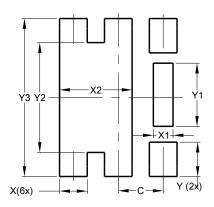


U-DFN2020-6									
	-	/pe E	•						
Dim	Min	Min Max Typ							
Α	0.57	0.63	0.60						
A1	0	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
b1	0.185	0.285	0.235						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
Е	1.95	2.05	2.00						
E2	1.40	1.60	1.50						
е	ı	1	0.65						
L	0.25	0.35	0.30						
L1	0.82	0.92	0.87						
K1	_	_	0.305						
K2	_	1	0.225						
Z	-	_	0.20						
All	Dimen	sions i	in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)			
С	0.650			
Х	0.400			
X1	0.285			
X2	1.050			
Υ	0.500			
Y1	0.920			
Y2	1.600			
Y3	2.300			



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